



8-Pin DIP High Speed Transistor Optocouplers

Single-Channel: 6N135M, 6N136M, HCPL4503M Dual-Channel: HCPL2530M, HCPL2531M

The 6N135M, 6N136M, HCPL4503M, HCPL2530M, and HCPL2531M optocouplers consist of an AlGaAs LED optically coupled to a high speed photodetector transistor for each channel.

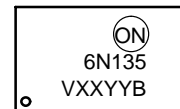
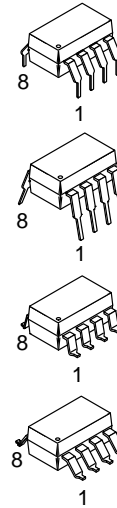
A separate connection for the bias of the photodiode improves the speed by several orders of magnitude over conventional phototransistor optocouplers by reducing the base collector capacitance of the input transistor.

The HCPL4503M has no internal connection to the phototransistor base for improved noise immunity. An internal noise shield provides superior common mode rejection of up to 50,000 V/ μ s.

- High Speed – 1 MBit/s
- Dual Channel: HCPL2530M, HCPL2531M
- CTR Guaranteed 0°C to 70°C
- No Base Connection for Improved Noise Immunity (HCPL4503M)
- Superior CMR of 15,000 V/ μ s Minimum (HCPL4503M)
- Safety and Regulatory Approvals
 - ◆ UL1577, 5,000 VAC_{RMS} for 1 Minute
 - ◆ DIN EN/IEC60747 5 5
- These are Pb Free Devices

- Line Receivers
- Pulse Transformer Replacement
- Output Interface to CMOS LSTTL TTL
- Wide Bandwidth Analog Coupling

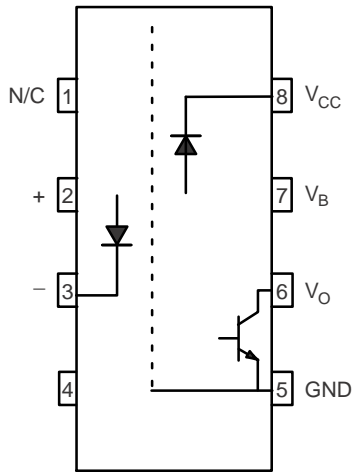
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- https://www.onsemi.com/products/interfaces/high_performance_optocouplers/high_performance_transistor_optocouplers/hcpl0500
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- https://www.onsemi.com/products/interfaces/high_performance_optocouplers/low_voltage_high_performance_optocouplers/fod0501



- 6N135 = Device Number
- V = DIN EN/IEC60747-5-5 Option (only appears on component ordered with this option)
- XX = Two Digit Year Code, e.g., '15'
- YY = Two Digit Work Week Ranging from '01' to '53'
- B = Assembly Package Code

See detailed ordering and shipping information on page 11 of this data sheet.

NOTE: Some of the devices on this data sheet have been . Please refer to the table on page 11.



6N135M, 6N136M,
HCPL4503M

HCPL2530M,
HCPL2531M

($T_A = 25^\circ\text{C}$ unless otherwise noted)

T_{STG}	Storage Temperature		-40 to +125	$^\circ\text{C}$
T_{OPR}	Operating Temperature		-40 to +100	$^\circ\text{C}$
T_J	Junction Temperature		-40 to +125	$^\circ\text{C}$
T_{SOL}	Lead Solder Temperature		260 for 10 s	$^\circ\text{C}$

I_F (avg)	DC/Average Forward Input Current Each Channel (Note 2)		25	mA
I_F (pk)	Peak Forward Input Current Each Channel (Note 3)	50% Duty Cycle, 1 ms P.W.	50	mA
I_F (trans)	Peak Transient Input Current Each Channel	$\leq 1 \mu\text{s}$ P.W., 300 pps	1.0	A
V_R	Reverse Input Voltage Each Channel		5	V
P_D	Input Power Dissipation Each Channel (Note 4)		45	mW

I_O (avg)	Average Output Current Each Channel		8	mA
I_O (pk)	Peak Output Current Each Channel		16	mA
V_{EBR}	Emitter-Base Reverse Voltage	6N135M and 6N136M	5	V
V_{CC}	Supply Voltage		-0.5 to 30	V
V_O	Output Voltage		-0.5 to 20	V
I_B	Base Current	6N135M and 6N136M	5	mA
P_D	Output Power Dissipation Each Channel (Note 5)			

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($V_{CC} = 5.0\text{ V}$, $T_A = 0^\circ\text{C}$ to 70°C unless otherwise specified.)

V_F	Input Forward Voltage	All	I_F
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(continued)

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(T_A = 0°C to 70°C unless otherwise specified.)

t _{PHL}	Propagation Delay Time to Logic LOW	6N135M	T _A



(continued)

(T _A = 25°C, unless otherwise noted.)							
V _{ISO}	Withstand Isolation Test Voltage	All	RH ≤ 50%, I _{I-O} ≤ 10 μA t = 1 minute, f = 50 Hz (Note 11) (Note 13)	5,000	–	–	VAC _{RMS}
R _{I-O}	Resistance (Input to Output)	All	V _{I-O} = 500 V _{DC} (Note 11)	–	10 ¹¹	–	Ω
C _{I-O}	Capacitance (Input to Output)	All	f = 1 MHz, V _{I-O} = 0 V _{DC} (Note 11)	–	1	–	pF
I _{I-I}	Input–Input Insulation Leakage Current	HCPL2530M, HCPL2531M	RH ≤ 45%, V _{I-I} = 500 V _{DC} , t = 5 s (Note 12)	–	<1	–	nA
R _{I-I}	Input–Input Resistance	HCPL2530M, HCPL2531M	V _{I-I} = 500 V _{DC} (Note 12)	–	10 ¹²	–	Ω
C _{I-I}	Input–Input Capacitance	HCPL2530M, HCPL2531M	f = 1 MHz (Note 12)	–	0.2	–	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

7. Current Transfer Ratio is defined as a ratio of output collector current, I_O, to the forward LED input current, I_F, times 100%.

8. The 4.1 kΩ load represents 1 LSTTL unit load of 0.36 mA and 6.1 kΩ pull-up resistor.

9. The 1.9 kΩ load represents 1 TTL unit load of 1.6 mA and 5.6 kΩ pull-up resistor.

10. Common mode transient immunity in logic high level is the maximum tolerable (positive) dV_{CM}/dt on the leading edge of the common mode pulse signal, V_{CM}, to assure that the output will remain in a logic high state (i.e., V_O > 2.0 V).

Common mode transient immunity in logic low level is the maximum tolerable (negative) dV_{CM}/dt on the trailing edge of the common mode pulse signal, V_{CM}, to assure that the output will remain in a logic low state (i.e., V_O < 0.8 V).

11. Device is considered a two terminal device: pins 1, 2, 3 and 4 are shorted together and pins 5, 6, 7 and 8 are shorted together.

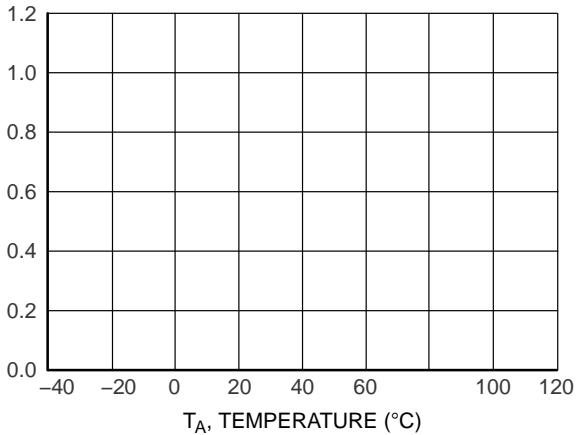
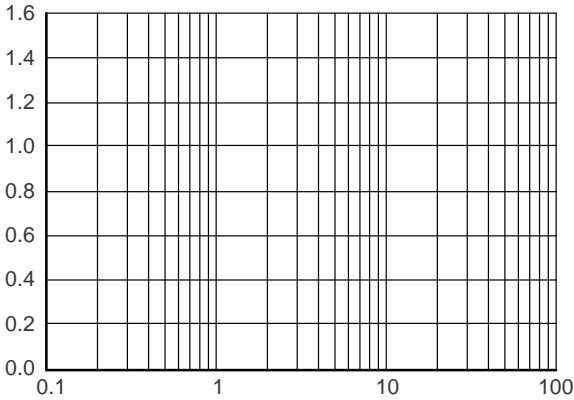
12. Measured between pins 1 and 2 shorted together, and pins 3 and 4 shorted together.

13. 5000 V_{RMS} for 1 minute duration is equivalent to 6000 V_{RMS} for 1 second duration.

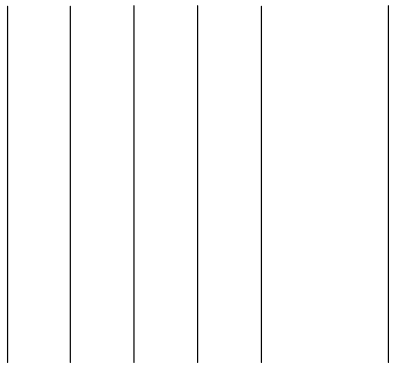
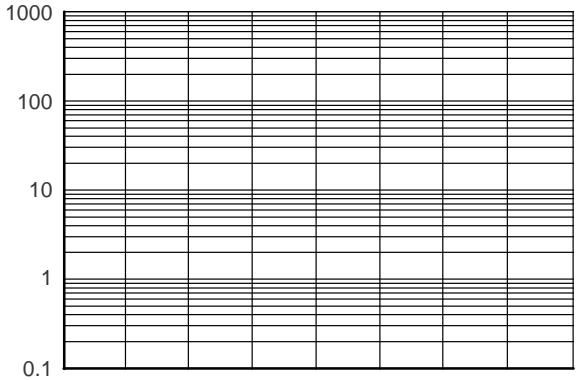
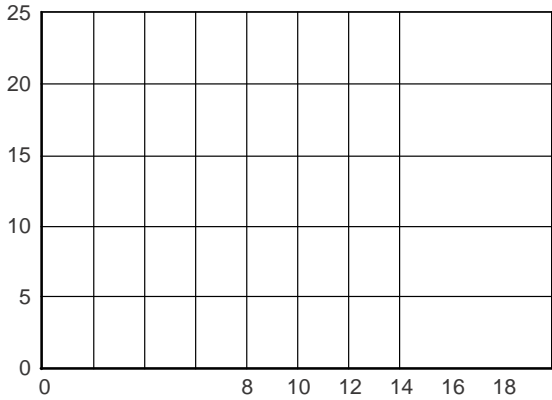
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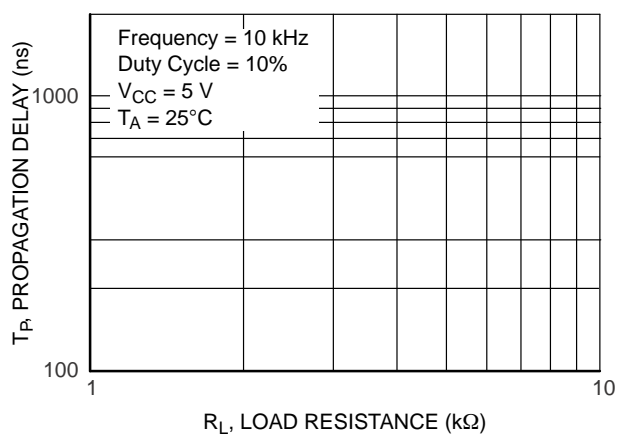
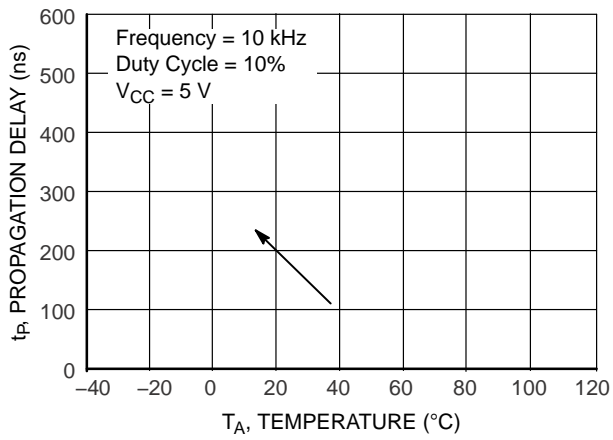
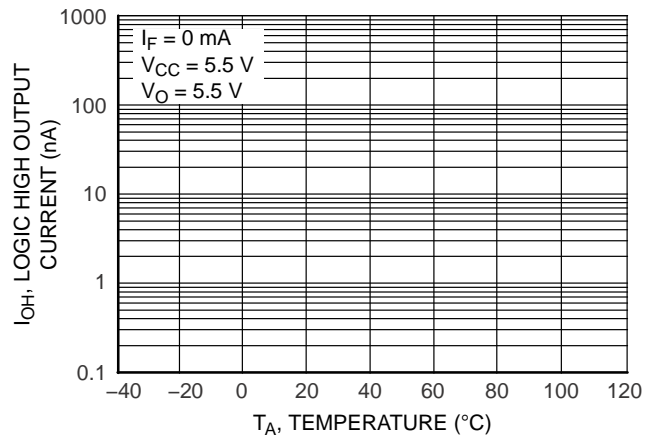
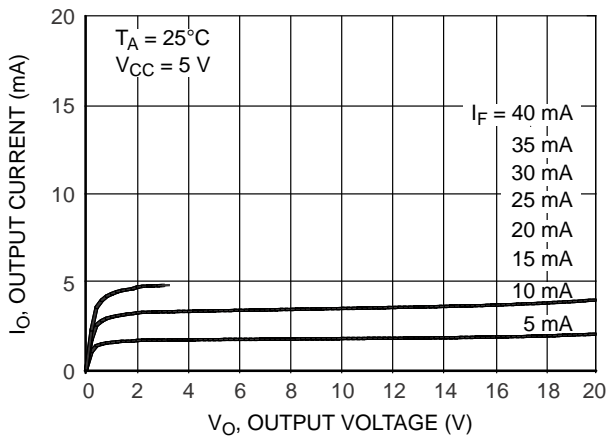
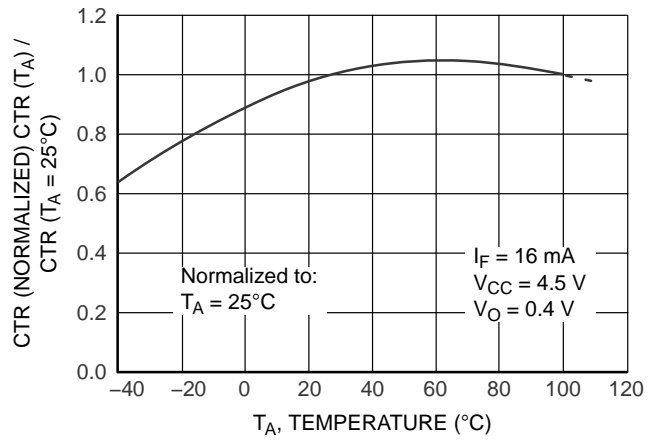
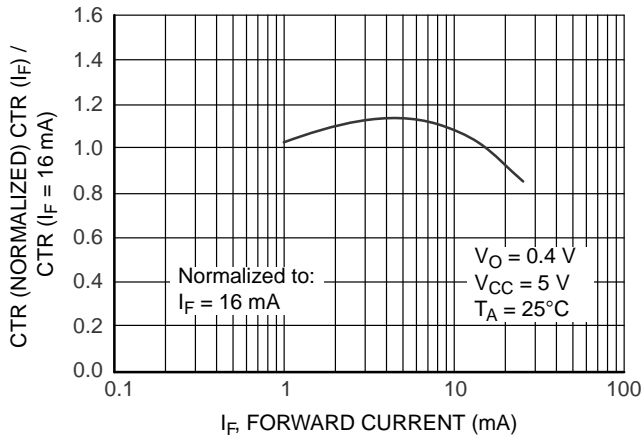
(For single-channel devices; 6N135M, 6N136M, and HCPL4503M.)



T_A, TEMPERATURE (°C)



(For dual-channel devices; HCPL2530M and HCPL2531M.)

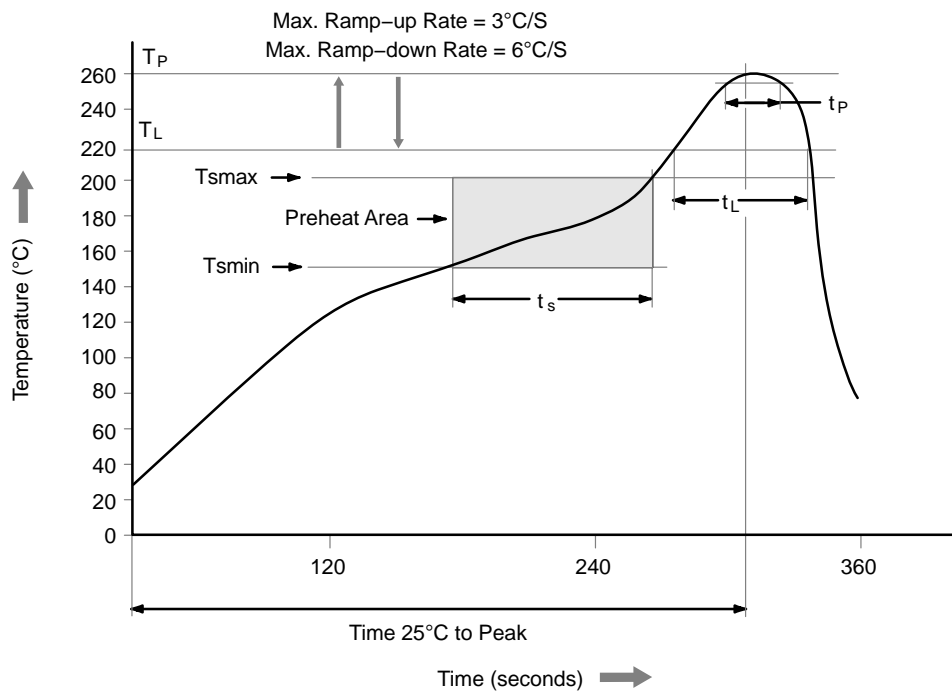


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	150°C
	200°C
	to 120 s

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6N135M	PDIP8 9.655x6.61, 2.54P DIP 8-Pin	50 Units / Tube
6N135SM	PDIP8 GW SMT 8-Pin (Lead Bend)	50 Units / Tube
6N135SDM	PDIP8 GW SMT 8-Pin (Lead Bend)	1,000 / Tape and Reel
6N135VM	PDIP8 9.655x6.61, 2.54P DIP 8-Pin, DIN IEC60747-5-5 Option	50 Units / Tube
6N135SVM	PDIP8 GW SMT 8-Pin (Lead Bend), DIN EN/IEC 60747-5-5 Option	50 Units / Tube
6N135SDVM	PDIP8 GW SMT 8-Pin (Lead Bend), DIN EN/IEC 60747-5-5 Option	1,000 / Tape and Reel
6N135TSVM	PDIP8 GW SMT 8-Pin, 0.4" Lead Spacing, DIN EN/IEC 60747-5-5 Option	50 Units / Tube
6N135TSR2VM	PDIP8 GW SMT 8-Pin, 0.4" Lead Spacing, DIN EN/IEC 60747-5-2 Option	1,000 / Tape and Reel

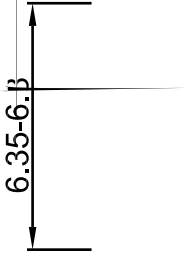
(Note 14)

6N135TVM	PDIP8 6.6x3.81, 2.54P DIP 8-Pin, 0.4" Lead Spacing, DIN EN/IEC 60747-5-5 Option	50 Units / Tube
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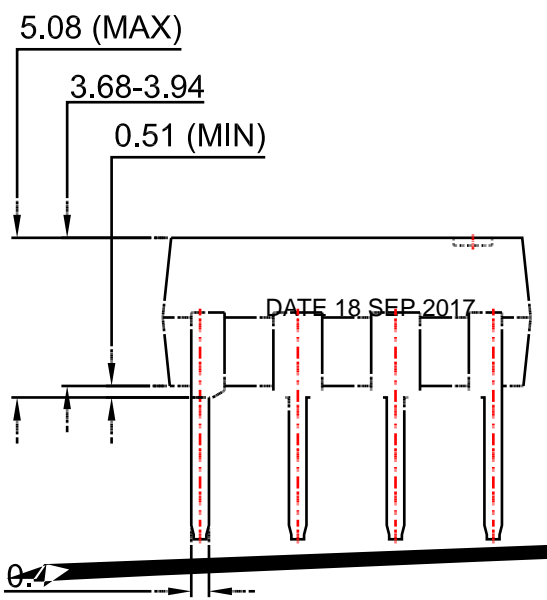
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PDIP8 6.6x3.81, 2.54P

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PDIP8 9.655x6.6, 2.54P
CASE 646CQ
ISSUE O



PDIP8 GW
CASE 709AC
ISSUE 0

LANE

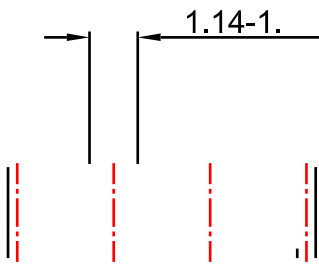
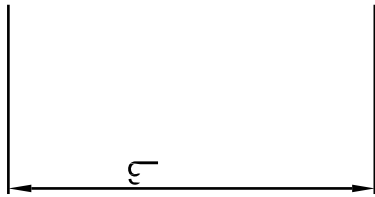
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TO THIS PACKAGE

PDIP8 GW
CASE 709AD
ISSUE O

DATE 31 JUL 2016

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NOTES:
A) NO STA C

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